

# **Quotation Request Form**

# **Behavioral Modeling Service – Active Device**

#### **Submitted by:**

Company Name :	Phone :	Web:	Email:
Contact :	Phone :	mobile :	Email:
Adress :			
Other Information :	Quotation Date :	Request Date :	Date model Needed :

#### **Submitted to:**

AMCAD-Engineering 20 Av Atlantis / ESTER TECHNOPOLE 87068 Limoges France

Contact

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Email: <u>info@amcad-engineering.com</u>

<u>Date :</u>	
Reference :	

### Type of Device to be Modeled or Characterized

Type of device	□HPA	□LNA		□Limiter	
Provide a short device description					
DC consumption behavior to be modeled	☐ Yes ☐ No		□No		
Device format	☐ Wafer	☐ Packaged *			
Data Sheet Available?	□No	☐ Yes, will provide		Yes, specify Web site	
RF Wafer Probe Compatibility?	□No	☐ Yes		Probe	e Pitch(  )
Are on-wafer calibration standards available?	□No			□ Y€	98
Is test fixture calibration kit available?	□No			□ Y€	es
Type and Size	Wafer, Reticule or Chip Size →			Package type & dimensions →	
Digital control?	□ No			☐ Y	es, will provide

<sup>\*</sup> Additional Information about the Device format:



# **Data & Test condition Requirement**

For active devices,	, we need informatior	about maximum	current/voltage/P	dc ratings, ge	eneral electrical
characteristics and	I layout drawing of the	e device and/or its	s package board of	geometry (if a	pplicable).

Absolute Max rating			
Gain compression (dB)			
MAX Output peak DC current (A)			
MAX Input peak DC current (A)			
MAX dissipated Power (W)			
Saturation Power (W)			
Max Input Power			

## **Measurement configuration**

### Device biasing

	Bias Conditions:	DC mode	Pulsed mode					
	List of bias conditions to be characterized:							
Diania a mada	Vin (V) (if applicable)							
Biasing modes	Vout (V) or Vdd (V)							
	Vin pulse width (µs)							
	Vout pulse width (μs)							
	Duty Cycle (%)							
Stop Conditions	Max Mean power consumption (W):							
	Max Peak power consumption (W):							
Temperature (°C)								

### • Power and frequency sweep

Fundamental	Start (GHz)		Stop (GHz)	Step (GHz)
Frequency (GHz)				
RF mode	CW mode / Pulsed mode			
	Pulse width (µs)			
	Duty cycle (%)			
Gain compression (dB)				
Noise Figure measurement?	□NO	□YES		

### Load pull

Number of impedance loads	□ 3	6	<u> </u>	<u>21</u>	☐ Custom pattern
Max TOS					



# **Model Capabilities**

<ul> <li>Definition of the RF Circu model</li> </ul>	it/System Simulator that will be used to simulate the
ADS (Keysight):	
SystemVue (Keysight):	
VSS (NI):	
Simulink (Matworks):	
Custom system simulator:	
Additional information about software	are version:
• Type of Simulation	
CW simulation:	
Envelop transient:	
Data Flow:	
• Type of Analysis	
Sweep:	
Noise:	
Statistical:	
Type of model needed	
Static model (no memory effect	s):
Dynamic model:	
RF Frequency dispersion be	havior (UHF): Yes/No
Low Frequency effect behav	ior (UHFLF): Yes/No
Mismatch Influence (BHF):	
Max VSWR:	
Additional Information Commen	ts/Requirements:

PLEASE E-MAIL TO: info@amcad-engineering.com